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in the following listed application(s) or patent(s) for which the issue fee has been paid.

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Respectfully Submitted,



Mark J. Murphy
Registration No. 34,225
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COOK, ALEX, McFARRON,
MANZO, CUMMINGS & MEHLER, Ltd.
200 West Adams Street
Suite 2850
Chicago, Illinois 60606
(312) 236-8500

Customer No: 26568



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(12) **United States Patent**
Yamazaki et al.

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- (54) **FERROELECTRIC LIQUID CRYSTAL AND GOGGLE TYPE DISPLAY DEVICES**
 (75) Inventors: **Shunpei Yamazaki**, Tokyo (JP); **Hiroki Adachi**, Kanagawa (JP)
 (73) Assignee: **Semiconductor Energy Laboratory Co., Ltd.** (JP)

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- (*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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Primary Examiner—Ori Nadav
 (74) *Attorney, Agent, or Firm*—Cook, Alex, McFarron, Manzo, Cummings & Mehler, Ltd.

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 (58) **Field of Classification Search** 257/347; 257/351, 344, 412, 69, 72; 438/305
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ABSTRACT

The present invention relates to a semiconductor device including a circuit composed of thin film transistors having a novel GOLD (Gate-Overlapped LDD (Lightly Doped Drain)) structure. The thin film transistor comprises a first gate electrode and a second electrode being in contact with the first gate electrode and a gate insulating film. Further, the LDD is formed by using the first gate electrode as a mask, and source and drain regions are formed by using the second gate electrode as the mask. Then, the LDD overlapping with the second gate electrode is formed. This structure provides the thin film transistor with high reliability.

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